## NSN 5962-01-290-2306

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-290-2306

| Overall Length:  1.290 inches  Overall Height:  0.425 inches  Body Length:  1.290 inches  Body Width:  Between 0.500 inches and 0.610 inches  Body Height:  Between 0.500 inches and 0.210 inches  Maximum Power Dissipation Rating:  1.1 waits  Operating Tempurature Range:  -55.0/+125.0 degrees celsius  Features Provided:  Electrostatic sensitive and programmed and hermetically sealed and burn in and schottky  Inclosure Material:  Ceramic  Dual-in-line  Output Logic Form:  Transistor-transistor logic  Input Circuit Pattern:  14 input  Case Outline Source And Designator:  D-3 mil-m-38510  Current Rating Per Characteristic:  185.00 millsamperes supply  Terminal Surface Treatment:  50.0der  Voltage Rating And Type Per Characteristic:  -0.5 volts power source and 7.0 volts power source  Time Rating Per Chacteristic:  90.00 nanoseconds access  Memory Device Type:  Prom  |
|---|
| Overall Height: 0.425 inches Body Length: 1.290 inches Body Width: Between 0.500 inches and 0.610 inches Body Height: Between 0.150 inches and 0.210 inches Maximum Power Dissipation Rating: 1.1 watts Operating Tempurature Range: -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius Features Provided: Electrostatic sensitive and programmed and hermetically sealed and burn in and schottky Inclosure Material: Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Transistor-transistor logic Input Circuit Pattern: 14 input Crase Outline Source And Designator: D-3 mil-m-38510 Current Rating Per Characteristic: 185.00 milliamperes supply Termial Surface Treatment: Solder Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source Time Rating Per Chacteristic: 90.00 nanoseconds access Memory Device Type:  |
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| 90.00 nanoseconds access  Memory Device Type:   |
| Memory Device Type:   |
|   |
| Prom  |
|   |
| Memory Capacity:  |
| Unknown   |
| Test Data Document:   |
| 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.  |
|   |

## NSN 5962-01-290-2306

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| Terminal Type Aı | nd Quantity: |
|------------------|--------------|
|------------------|--------------|

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0